

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2715	428/428	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 20:16
L2	4510	428/446	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 20:33
L3	2	"20030003765"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 20:27
L4	7581	428/447	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 20:50
L5	1607	428/448	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 21:08
L6	6086	428/209	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 21:21
L7	2398	428/210	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 21:38
L8	3489	428/901	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 21:55

L9	1277	257/760	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 22:12
L10	395	438/760	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 22:12
S1	73	"6140226"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:58
S2	0	"6140226" and "Sioc-h"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:58
S3	0	257/758 and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:01
S4	2	"257"/\$.ccls. and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:01
S5	3	"438"/\$.ccls. and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:59
S6	0	"361"/\$.ccls. and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:59
S7	0	"29"/\$.ccls. and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:59
S8	0	"174"/\$.ccls. and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:00

S9	3	(semiconductor or die or chip or IC) and "SiOC-H"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:00
S10	69	(semiconductor or die or chip or IC) and "SiOCH"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:00
S11	6	257/758 and "SiOCH"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:01
S12	43	"257"/\$.ccls. and "SiOCH"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:04
S13	48	"438"/\$.ccls. and "SiOCH"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 18:04
S14	877	wafer and 257/48	USPAT	OR	ON	2004/06/14 01:20
S15	1554	257/48	USPAT	OR	ON	2004/06/14 00:38
S16	1	"4968931".PN.	USPAT	OR	OFF	2004/06/14 01:01
S17	1	"5504369".PN.	USPAT	OR	OFF	2004/06/14 01:02
S18	1	"5898186".PN.	USPAT	OR	OFF	2004/06/14 01:02
S19	1	"5962868".PN.	USPAT	OR	OFF	2004/06/14 01:05
S20	1	"6057171".PN.	USPAT	OR	OFF	2004/06/14 01:05
S21	1	"6175125".PN.	USPAT	OR	OFF	2004/06/14 01:05
S22	1	"6218848".PN.	USPAT	OR	OFF	2004/06/14 01:05
S23	1	"6281696".PN.	USPAT	OR	OFF	2004/06/14 01:06
S24	1	"6362638".PN.	USPAT	OR	OFF	2004/06/14 01:06
S25	1	"5292343".PN.	USPAT	OR	OFF	2004/06/14 01:08
S26	1	"5389556".PN.	USPAT	OR	OFF	2004/06/14 01:09
S27	1	"5391188".PN.	USPAT	OR	OFF	2004/06/14 01:10
S28	1	"5489538".PN.	USPAT	OR	OFF	2004/06/14 01:10
S29	1	"5532174".PN.	USPAT	OR	OFF	2004/06/14 01:10
S30	1	"5600257".PN.	USPAT	OR	OFF	2004/06/14 01:11
S31	1	"5532174".PN.	USPAT	OR	OFF	2004/06/14 01:11
S32	1	"5241266".PN.	USPAT	OR	OFF	2004/06/14 01:17
S33	1	"5254942".PN.	USPAT	OR	OFF	2004/06/14 01:17

S34	1	"5329471".PN.	USPAT	OR	OFF	2004/06/14 01:18
S35	1	"5396170".PN.	USPAT	OR	OFF	2004/06/14 01:18
S36	1	"5396170".PN.	USPAT	OR	OFF	2004/06/14 01:18
S37	1	"5408129".PN.	USPAT	OR	OFF	2004/06/14 01:18
S38	1	"5898186".PN.	USPAT	OR	OFF	2004/06/14 01:18
S39	1	"6233184".PN.	USPAT	OR	OFF	2004/06/14 01:18
S40	1	"6404660".PN.	USPAT	OR	OFF	2004/06/14 01:19
S41	1	"6411116".PN.	USPAT	OR	OFF	2004/06/14 01:19
S42	1	"6504359".PN.	USPAT	OR	OFF	2004/06/14 01:20
S43	47	"5389556"	USPAT	OR	ON	2004/06/14 01:24
S44	33	"5532174"	USPAT	OR	ON	2004/06/14 02:22
S45	9	"5327074"	USPAT	OR	ON	2004/06/14 02:56
S46	613440	switch	USPAT	OR	ON	2004/06/14 02:56
S47	40223	switch\$3 near transistor	USPAT	OR	ON	2004/06/14 02:56
S48	28311	switch\$3 adj transistor	USPAT	OR	ON	2004/06/14 02:57
S49	21862	switching adj transistor	USPAT	OR	ON	2004/06/14 03:13
S50	25	(switching adj transistor) and 257/48	USPAT	OR	ON	2004/06/14 02:57
S51	6	switching adj transistor with pad with (chip or dice or die)	USPAT	OR	ON	2004/06/14 03:14
S52	1383	257/734	USPAT	OR	OFF	2004/06/14 05:20
S53	591	257/620	USPAT	OR	OFF	2004/06/14 05:20
S54	798	257/620	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:22
S55	1917	257/691	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:24
S56	540	257/665	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:26
S57	2317	257/698	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:36

S58	405	257/698	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:30
S59	0	257/698 not 257/698	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:30
S60	1912	257/698 not 257/698	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:34
S61	4	"5494859".pn. or "6037664".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:35
S62	3299	257/773	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:45
S63	2690	257/773	USPAT	OR	OFF	2004/06/14 05:37
S64	609	257/773 not 257/773	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:39
S65	849	257/735	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:49
S66	678	257/741	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:51
S67	2	"5913147".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 05:50
S68	2761	438/14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:03



S69	396	438/14	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:01
S70	2365	438/14 not 438/14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:03
S71	863	438/462	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:13
S72	221	barrier with (silicon near nitride or "Si" near "N") same (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 07:28
S73	157	barrier with (silicon near nitride or "Si" near "N") same barrier with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 07:44
S74	5610	324/765	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:31
S75	1805	324/765	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:14
S76	3805	324/765 not 324/765	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:21
S77	1753	324/765 not 324/765 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:23
S78	1264	324/763	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:41

S79	1290	324/760	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:46
S80	2	325/201	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/14 06:50
S81	7	barrier near multi\$4 near (film or layer) same ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 07:27
S82	10397	barrier near (films or layers) same ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 07:27
S83	64	(barrier with (silicon near nitride or "Si" near "N") same (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper)) not (barrier with (silicon near nitride or "Si" near "N") same barrier with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 07:28
S84	78	barrier with (silicon near nitride or "Si" near "N") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:00
S85	1	"5162258".PN.	USPAT	OR	OFF	2004/06/14 07:58
S86	1	"5812364".PN.	USPAT	OR	OFF	2004/06/14 07:59
S87	1	"5913126".PN.	USPAT	OR	OFF	2004/06/14 07:59
S88	1	"5918135".PN.	USPAT	OR	OFF	2004/06/14 07:59
S89	1	"5920775".PN.	USPAT	OR	OFF	2004/06/14 07:59
S90	78	barrier with (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:00
S91	78	barrier with (silicon near nitride or "Si.sub.3N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:01

S92	113	barrier same (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:16
S93	446	barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:16
S94	59	barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:25
S95	93	(silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 11:17
S96	34	( (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)) not (barrier and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:42
S97	3066	silicon near nitride with dielectric near constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 09:29
S98	1831	silicon near nitride with dielectric near constant	USPAT	OR	ON	2004/06/14 09:38
S99	1	("FSO") with dielectric near constant	USPAT	OR	ON	2004/06/14 09:39
S100	1	("FSO" or "fluonated silicon oxide") with dielectric near constant	USPAT	OR	ON	2004/06/14 09:39
S101	1	("FSO" or fluonat\$3 near silicon near oxide) with dielectric near constant	USPAT	OR	ON	2004/06/14 09:45



S10 2	1	(siliconoxynitride) with dielectric near constant	USPAT	OR	ON	2004/06/14 09:40
S10 3	183	(bpsg) with dielectric near constant	USPAT	OR	ON	2004/06/14 10:07
S10 4	1605	257/750	USPAT	OR	ON	2004/06/14 10:12
S10 5	2141	257/751	USPAT	OR	ON	2004/06/14 10:21
S10 6	987	257/752	USPAT	OR	ON	2004/06/14 10:22
S10 7	3439	257/758	USPAT	OR	OFF	2004/06/16 11:15
S10 8	3	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") near (film or layer) same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 11:18
S10 9	41	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") same (silicon near dioxide or "Si" near "O.sub.2") same (passivation or protective or cover) near (layer or film) and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 11:24
S11 0	358	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") same (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 11:24
S11 1	553	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 15:13
S11 2	2	"20030003765"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 12:45
S11 3	2253	257/758 and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 13:16
S11 4	1700	(257/758 and ("Cu" or copper)) not (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:16

S11 5	382	257/751 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 15:56
S11 6	182	257/752 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:07
S11 7	791	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:08
S11 8	802	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:08
S11 9	590	257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2" or "SiO") and ("Cu" or copper)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:09
S12 0	37	(257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4" or "SiN") and (silicon near dioxide or "Si" near "O.sub.2" or "SiO") and ("Cu" or copper)) not (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon near dioxide or "Si" near "O.sub.2") and ("Cu" or copper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 16:09
S12 1	1612	257/758 not (257/758 and ("Cu" or copper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/16 17:47
S12 2	2128	257/750	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 12:49
S12 3	2675	257/751	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 12:52

S12 4	1132	257/752	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 13:09
S12 5	4998	257/758	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 13:15
S12 6	3774	257/758	USPAT	OR	OFF	2004/11/18 13:20
S12 7	1224	S125 not S126	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 13:42
S12 8	1289	174/258	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 13:55
S12 9	1378	174/256	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/18 19:52